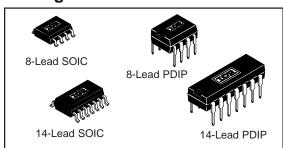


HIGH AND LOW SIDE DRIVER

Features

- Floating channel designed for bootstrap operation Fully operational to +600V
 Tolerant to negative transient voltage dV/dt immune
- Gate drive supply range from 10 to 20V (IR2106(4))
- Undervoltage lockout for both channels
- 3.3V, 5V and 15V input logic compatible
- Matched propagation delay for both channels
- Logic and power ground +/- 5V offset.
- Lower di/dt gate driver for better noise immunity
- Outputs in phase with inputs (IR2106)
- Also available LEAD-FREE

Packages



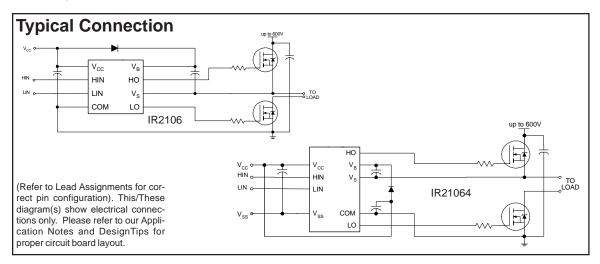
Description

The IR2106(4)(S) are high voltage, high speed power MOSFET and IGBT drivers with independent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output,

2106/2301//2108//2109/2302/2304Feature Comparison

Part	Input logic	Cross- conduction prevention logic	Dead-Time	Ground Pins	Ton/Toff	
2106/2301	HIN/LIN	no	none	COM	220/200	
21064	HIIN/LIIN	110	none	VSS/COM	220/200	
2108	HIN/LIN	1/00	Internal 540ns	COM	220/200	
21084	HIIN/LIIN	yes	Programmable 0.54~5µs	VSS/COM	220/200	
2109/2302	IN/SD	ves	Internal 540ns	COM	750/200	
21094	IIV/SD	yes	Programmable 0.54~5μs	VSS/COM	750/200	
2304	HIN/LIN	yes	Internal 100ns	СОМ	160/140	

down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.



Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units	
V _B	High side floating absolute voltage		-0.3	625	
Vs	High side floating supply offset voltage		V _B - 25	V _B + 0.3	1
V _{HO}	High side floating output voltage		V _S - 0.3	V _B + 0.3	
Vcc	Low side and logic fixed supply voltage		-0.3	25	
V _{LO}	Low side output voltage		-0.3	V _{CC} + 0.3	V
V _{IN}	Logic input voltage		V _{SS} - 0.3	V _{CC} + 0.3	
V _{SS}	Logic ground (IR21064 only)		V _{CC} - 25	V _{CC} + 0.3	
dVs/dt	Allowable offset supply voltage transient		_	50	V/ns
PD	Package power dissipation @ T _A ≤ +25°C	(8 lead PDIP)	_	1.0	
		(8 lead SOIC)	_	0.625	
		(14 lead PDIP)	_	1.6	W
		(14 lead SOIC)	_	1.0	Ī
Rth _{JA}	Thermal resistance, junction to ambient	(8 lead PDIP)	_	125	
		(8 lead SOIC)	_	200	
		(14 lead PDIP)	_	75	°C/W
		(14 lead SOIC)	_	120	
TJ	Junction temperature		_	150	
T _S	Storage temperature		-50	150	°C
TL	Lead temperature (soldering, 10 seconds)		_	300	

Recommended Operating Conditions

The Input/Output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The V_S and V_{SS} offset rating are tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
VB	High side floating supply absolute voltage IR2106(4)	V _S + 10	V _S + 20	
Vs	High side floating supply offset voltage	Note 1	600	
V _{HO}	High side floating output voltage	Vs	V _B	
V _{CC}	Low side and logic fixed supply voltage IR2106(4)	10	20	V
V _{LO}	Low side output voltage	0	Vcc	
V _{IN}	Logic input voltage	V _{SS}	V _C C	
V _{SS}	Logic ground (IR21064 only)	-5	5	
T _A	Ambient temperature	-40	125	°C

Note 1: Logic operational for V_S of -5 to +600V. Logic state held for V_S of -5V to -V_{BS}. (Please refer to the Design Tip DT97-3 for more details).

Dynamic Electrical Characteristics

 V_{BIAS} (V_{CC}, V_{BS}) = 15V, V_{SS} = COM, C_L = 1000 pF, T_A = 25°C.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
ton	Turn-on propagation delay	_	220	300		V _S = 0V
toff	Turn-off propagation delay	_	200	280		V _S = 0V or 600V
MT	Delay matching, HS & LS turn-on/off	_	0	30	nsec	
tr	Turn-on rise time	_	150	220		Vs = 0V
tf	Turn-off fall time	_	50	80		V _S = 0V

IR2106(4)(S)&(PBF)

International

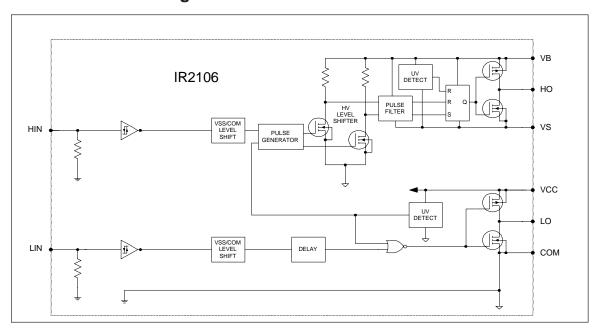
TOR Rectifier

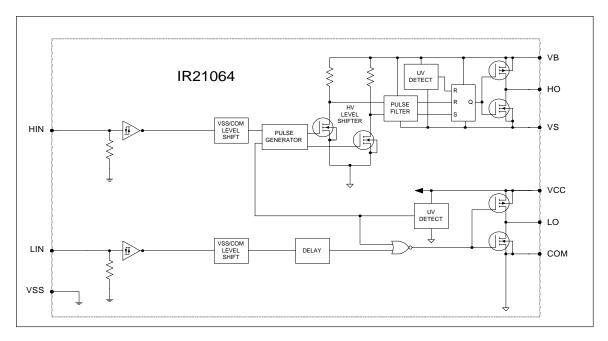
Static Electrical Characteristics

 V_{BIAS} (V_{CC}, V_{BS}) = 15V, V_{SS} = COM and T_A = 25°C unless otherwise specified. The V_{IL}, V_{IH} and I_{IN} parameters are referenced to V_{SS}/COM and are applicable to the respective input leads. The V_O, I_O and Ron parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
V _{IH}	Logic "1" input voltage (IR2106(4))	2.9	_	_		V _{CC} = 10V to 20V
V _{IL}	Logic "0" input voltage (IR2106(4))	_	_	0.8	V	V _{CC} = 10V to 20V
V _{OH}	High level output voltage, V _{BIAS} - V _O	_	0.8	1.4	V	I _O = 20 mA
V _{OL}	Low level output voltage, VO	_	0.3	0.6		I _O = 20 mA
I _{LK}	Offset supply leakage current	_	_	50		V _B = V _S = 600V
I _{QBS}	Quiescent V _{BS} supply current	20	75	130		V _{IN} = 0V or 5V
IQCC	Quiescent V _{CC} supply current	60	120	180		V _{IN} = 0V or 5V
I _{IN+}	Logic "1" input bias current				μΑ	
	$V_{IN} = 5V (IR2106(4))$	_	5	20		
I _{IN-}	Logic "0" input bias current					
	$V_{IN} = 0V (IR2106(4))$	_	_	2		
V _{CCUV+}	V _{CC} and V _{BS} supply undervoltage positive going	8.0	8.9	9.8		
V _{BSUV+}	threshold					
V _{CCUV} -	V _{CC} and V _{BS} supply undervoltage negative going	7.4	8.2	9.0	V	
V _{BSUV} -	threshold				-	
VCCUVH	Hysteresis	0.3	0.7	_		
V _{BSUVH}						
I _{O+}	Output high short circuit pulsed current	120	200	_		$V_O = 0V$,
					mA	PW ≤ 10 µs
I _{O-}	Output low short circuit pulsed current	250	350	-		$V_0 = 15V$,
						PW ≤ 10 μs

Functional Block Diagrams





IR2106(4)(S) & (PBF)

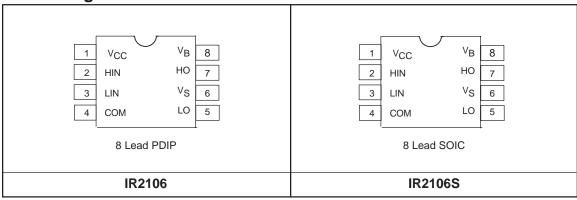
International

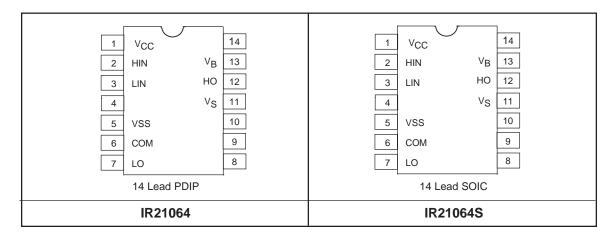
TOR Rectifier

Lead Definitions

Symbol	Description
HIN	Logic input for high side gate driver output (HO), in phase
LIN	Logic input for low side gate driver output (LO), in phase
VSS	Logic Ground (IR21064 only)
V _B	High side floating supply
НО	High side gate drive output
Vs	High side floating supply return
V _{CC}	Low side and logic fixed supply
LO	Low side gate drive output
COM	Low side return

Lead Assignments





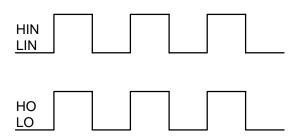


Figure 1. Input/Output Timing Diagram

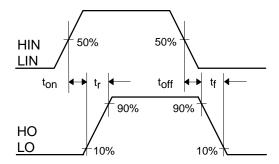


Figure 2. Switching Time Waveform Definitions

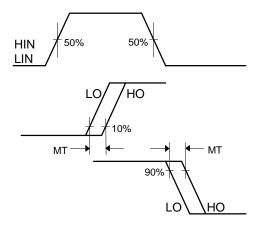


Figure 3. Delay Matching Waveform Definitions

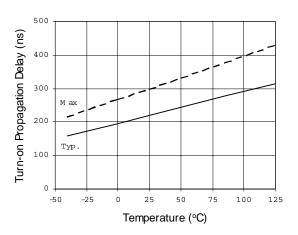


Figure 4A. Turn-on Propagation Delay vs. Temperature

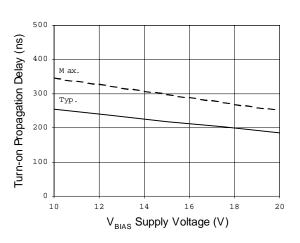


Figure 4B. Turn-on Propagation Delay vs. Supply Voltage

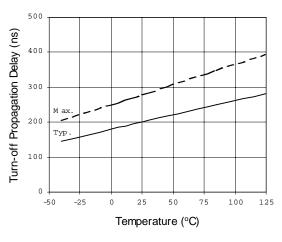


Figure 5A. Turn-off Propagation Delay vs. Temperature

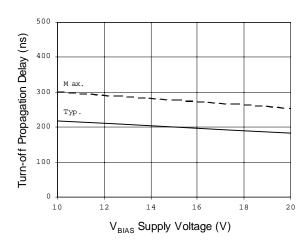


Figure 5B. Turn-off Propagation Delay vs. Supply Voltage

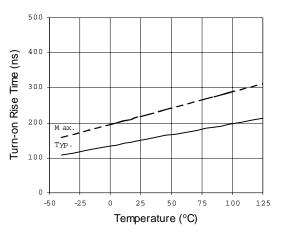


Figure 6A. Turn-on Rise Time vs. Temperature

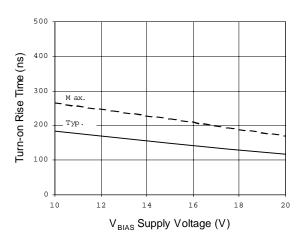


Figure 6B. Turn-on Rise Time vs. Supply Voltage

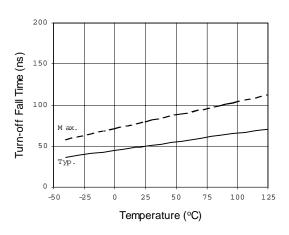


Figure 7A. Turn-off Fall Time vs. Temperature

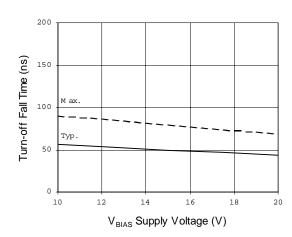


Figure 7B. Turn-off Fall Time vs. Supply Voltage

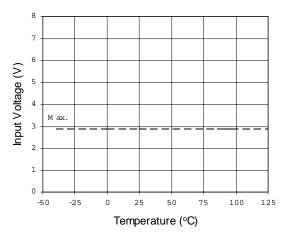


Figure 8A. Logic "1" Input Voltage vs. Temperature

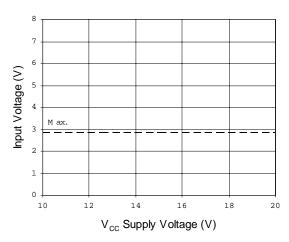


Figure 8B. Logic "1" Input Voltage vs. Supply Voltage

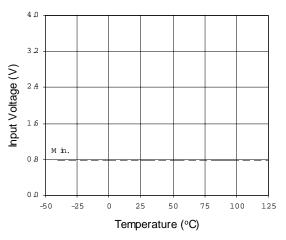


Figure 9A. Logic "0" Input Voltage vs. Temperature

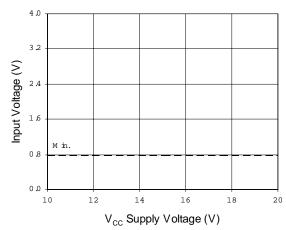


Figure 9B. Logic "0" Input Voltage vs. Supply Voltage

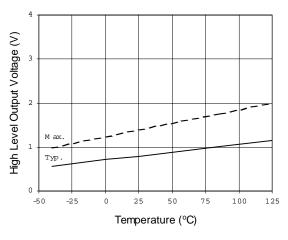


Figure 10A. High Level Output Voltage vs. Temperature

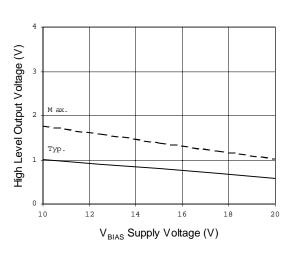


Figure 10B. High Level Output Voltage vs. Supply Voltage

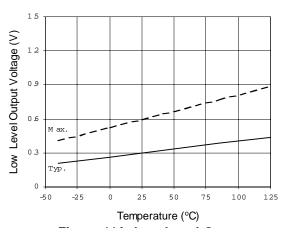


Figure 11A. Low Level Output Voltage vs. Temperature

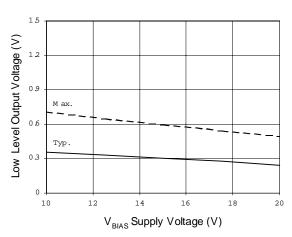


Figure 11B. Low Level Output Voltage vs. Supply Voltage

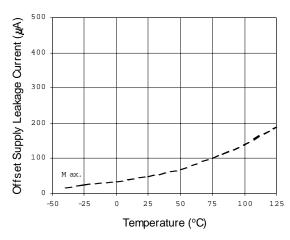


Figure 12A. Offset Supply Leakage Current vs. Temperature

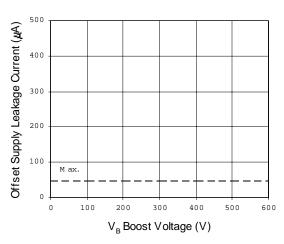


Figure 12B. Offset Supply Leakage Current vs. Supply Voltage

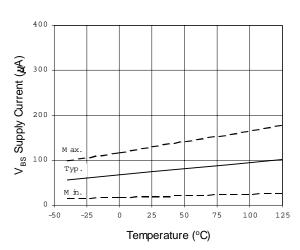


Figure 13A. VBS Supply Current vs. Temperature

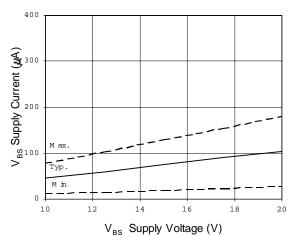


Figure 13B. VBS Supply Current vs. Supply Voltage

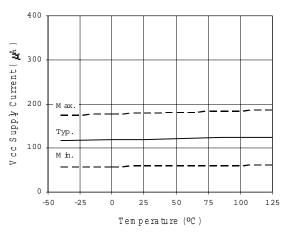


Figure 14A. Quiescent V_{CC} Supply Current vs. Temperature

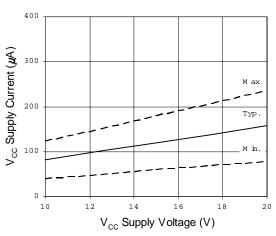


Figure 14B. Quiescent VCC Supply Current vs. VCC Supply Voltage

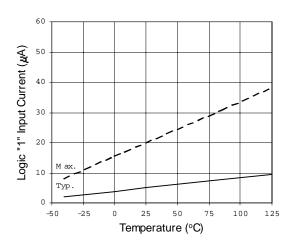


Figure 15A. Logic "1" Input Current vs. Temperature

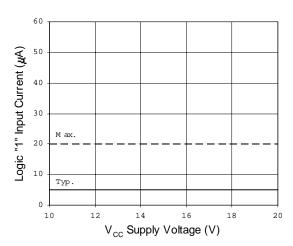


Figure 15B. Logic "1" Bias Current vs. Supply Voltage

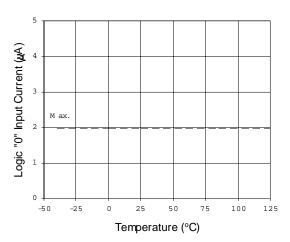


Figure 16A. Logic "0" Input Current vs. Temperature

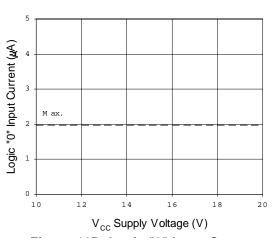


Figure 16B. Logic "0" Input Currentt vs. Supply Voltage

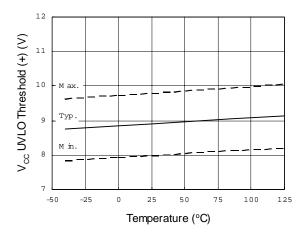


Figure 17. VCC Undervoltage Threshold (+) vs. Temperature

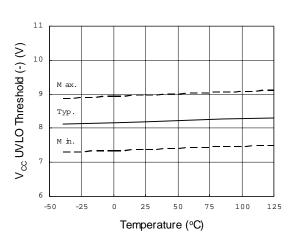


Figure 18. VCC Undervoltage Threshold (-) vs. Temperature

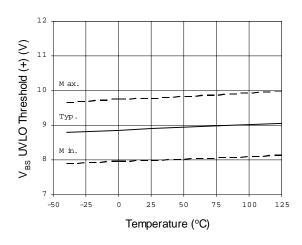


Figure 19. VBS Undervoltage Threshold (+) vs. Temperature

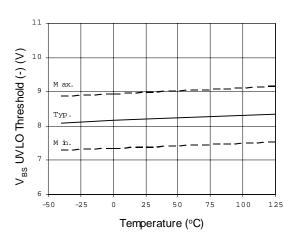


Figure 20. VBS Undervoltage Threshold (-) vs. Temperature

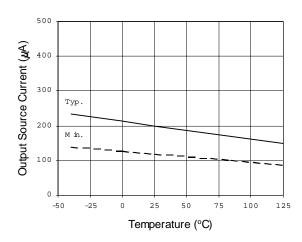


Figure 21A. Output Source Current vs. Temperature

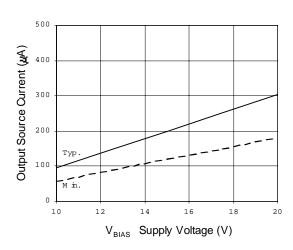


Figure 21B. Output Source Current vs. Supply Voltage

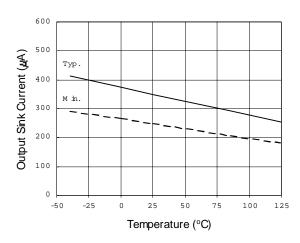


Figure 22A. Output Sink Current vs. Temperature

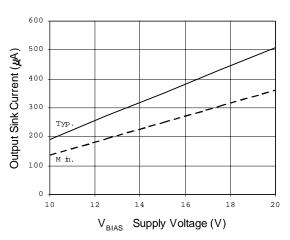


Figure 22B. Output Sink Currentt vs. Supply Voltage

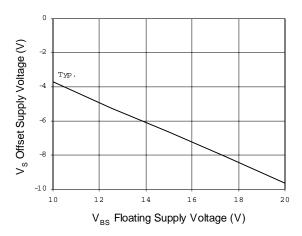


Figure 23. Maximum V_S Negative Offset vs. Supply Voltage

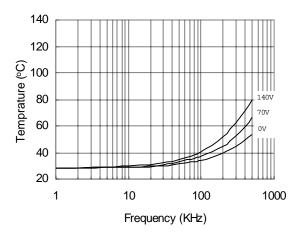


Figure 24. IR2106 vs. Frequency (IRFBC20), Rgate=33 Ω , VCC=15V

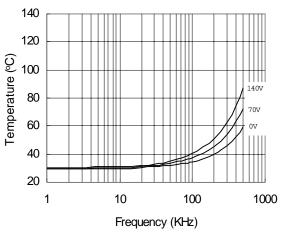


Figure 25. IR2106 vs. Frequency (IRFBC30), ${\rm R_{\rm cate}}{=}22\Omega,\,{\rm V_{\rm cc}}{=}15{\rm V}$

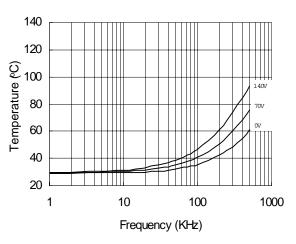


Figure 26. IR2106 vs. Frequency (IRFBC40), $R_{\text{qate}} \! = \! 15 \Omega, \, V_{\text{CC}} \! = \! 15 V$

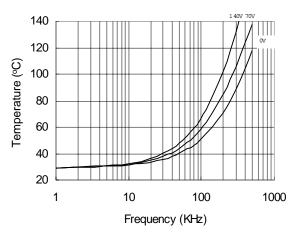


Figure 27. IR2106 vs. Frequency (IRFPE50), $R_{\text{qate}} {=} 10 \Omega, \, V_{\text{CC}} {=} 15 V$

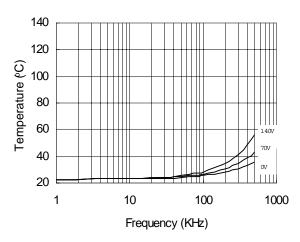


Figure 28. IR21064 vs. Frequency (IRFBC20), ${\rm R_{\rm qate}}{=}33\Omega, {\rm V_{CC}}{=}15{\rm V}$

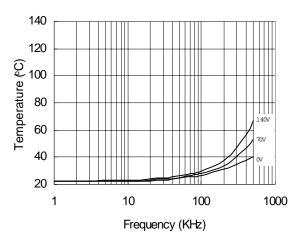


Figure 29. IR21064 vs. Frequency (IRFBC30), $R_{\text{cate}} \!\!=\!\! 22\Omega, V_{\text{CC}} \!\!=\!\! 15V$

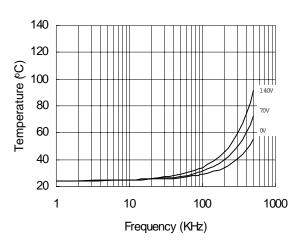


Figure 30. IR21064 vs. Frequency (IRFBC40), R_{cate} =15 Ω , V_{cc} =15V

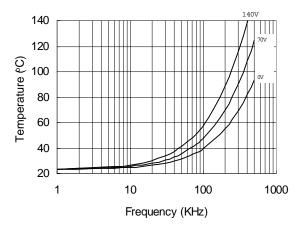
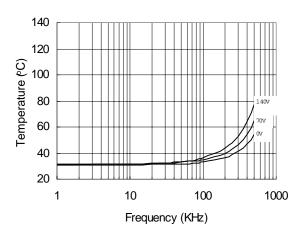


Figure 31. IR21064 vs. Frequency (IRFPE50), $R_{\text{uate}}\text{=}10\Omega,\,V_{\text{CC}}\text{=}15\text{V}$



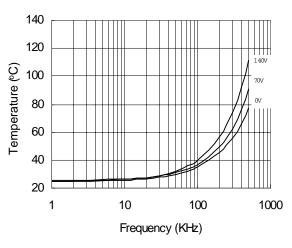


Figure 33. IR2106S vs. Frequency (IRFBC30), $R_{\text{cate}}\text{=}22\Omega, \, \text{V}_{\text{CC}}\text{=}15\text{V}$

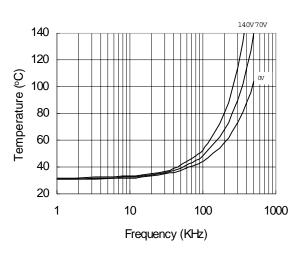


Figure 34. IR2106S vs. Frequency (IRFBC40), $R_{\text{qate}} \! = \! \! 15\Omega, \, V_{\text{CC}} \! = \! \! 15V$

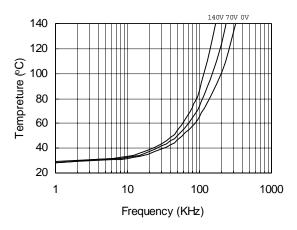


Figure 35. IR2106S vs. Frequency (IRFPE50), $R_{\text{gate}} \! = \! 10\Omega$, $V_{\text{CC}} \! = \! 15V$

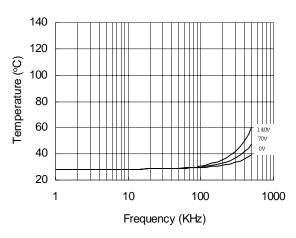


Figure 36. IR21064S vs. Frequency (IRFBC20), ${\rm R_{\rm qate}}{=}33\Omega,\,{\rm V_{\rm CC}}{=}15{\rm V}$

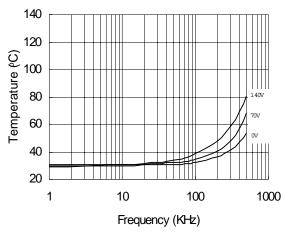


Figure 37. IR21064S vs. Frequency (IRFBC30), $R_{\text{qate}}\text{=}22\Omega,\,V_{\text{CC}}\text{=}15\text{V}$

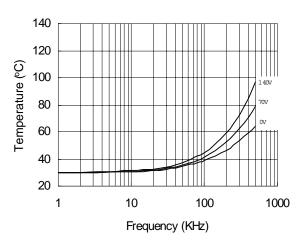


Figure 38. IR21064S vs. Frequency (IRFBC40), ${\rm R_{gate}}{=}15\Omega,\,{\rm V_{CC}}{=}15{\rm V}$

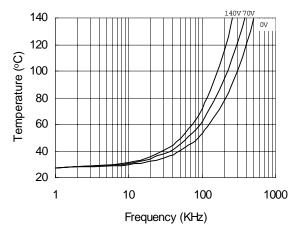
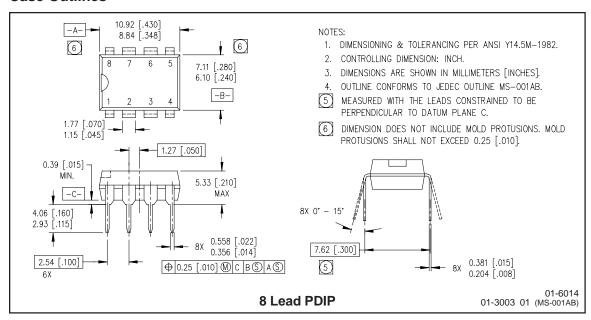


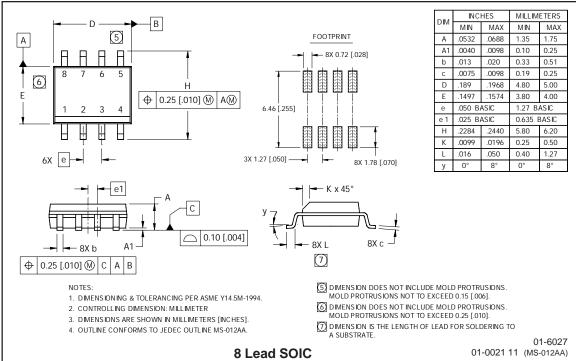
Figure 39. IR21064S vs. Frequency (IRFPE50), $\rm R_{gate} {=} 10\Omega,\, \rm V_{CC} {=} 15V$

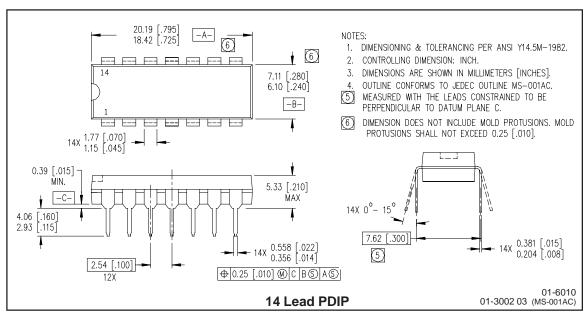
International TOR Rectifier

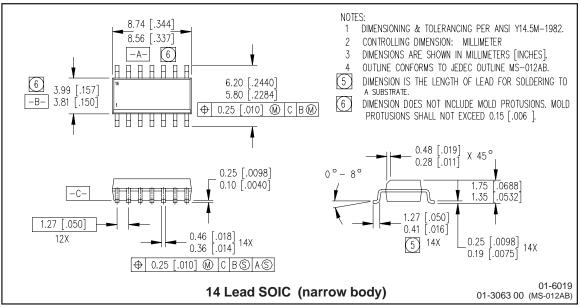
IR2106(4)(S & (PbF))

Case Outlines

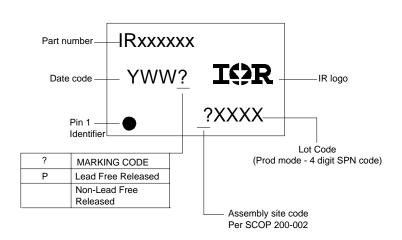








LEADFREE PART MARKING INFORMATION



ORDER INFORMATION

Basic Part (Non-Lead Free)

8-Lead PDIP IR2106 order IR2106 8-Lead SOIC IR2106S order IR2106S 14-Lead PDIP IR21064 order IR21064 14-Lead SOIC IR21064S order IR21064S

Leadfree Part

8-Lead PDIP IR2106 order IR2106PbF 8-Lead SOIC IR2106S order IR2106SPbF 14-Lead PDIP IR21064 order IR21064PbF 14-Lead SOIC IR21064S order IR21064SPbF

International

TOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245 Tel: (310) 252-7105

This product has been qualified per industrial level

Data and specifications subject to change without notice. 4/12/2004